Switching Transistors

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	15	Vdc
Collector – Emitter Voltage	V _{CES}	40	Vdc
Collector – Base Voltage	V _{CBO}	40	Vdc
Emitter-Base Voltage	V _{EBO}	4.5	Vdc
Collector Current – Continuous	Ι _C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

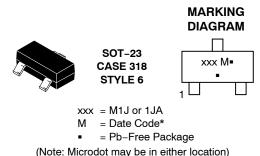
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

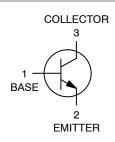


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*Date Code orientation and/or overbar may vary depending upon manufacturing location.



ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2369LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT2369LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT2369LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT2369ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT2369ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

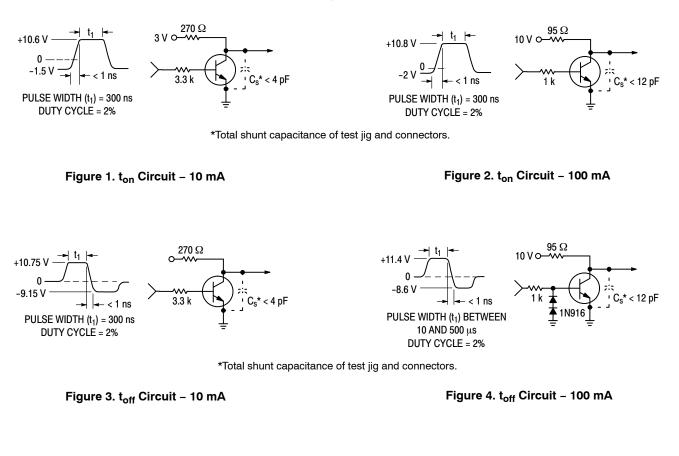
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	15	-	_	Vdc
Collector – Emitter Breakdown Voltage $(I_C = 10 \ \mu Adc, \ V_{BE} = 0)$	V _{(BR)CES}	40	-	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	40	-	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	4.5	_	_	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$) ($V_{CB} = 20 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C}$)	I _{СВО}			0.4 30	μAdc
Collector Cutoff Current MMBT2369A (V _{CE} = 20 Vdc, V _{BE} = 0)	I _{CES}	-	_	0.4	μAdc
ON CHARACTERISTICS		•	•	•	
$\begin{array}{l} \text{DC Current Gain (Note 3)} \\ \text{MMBT2369 (I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 0.35 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 10 \text{ mAdc, V}_{CE} = 0.35 \text{ Vdc}, \text{T}_{A} = -55^{\circ}\text{C}) \\ \text{MMBT2369A (I}_{C} = 30 \text{ mAdc, V}_{CE} = 0.4 \text{ Vdc}) \\ \text{MMBT2369 (I}_{C} = 100 \text{ mAdc, V}_{CE} = 2.0 \text{ Vdc}) \\ \text{MMBT2369A (I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc}) \\ \end{array}$	h _{FE}	40 - 20 30 20 20	- - - - - - -	120 120 - - - - -	_
$\begin{array}{l} \mbox{Collector} - \mbox{Emitter Saturation Voltage (Note 3)} \\ \mbox{MMBT2369} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 10 \mbox{ mAdc}, I_{B} = 1.0 \mbox{ mAdc}, T_{A} = +125^{\circ}\mbox{C}) \\ \mbox{MMBT2369A} (I_{C} = 30 \mbox{ mAdc}, I_{B} = 3.0 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MMBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox{ mAdc}, I_{B} = 10 \mbox{ mAdc}) \\ \mbox{MBT2369A} (I_{C} = 100 \mbox$	V _{CE(sat)}		- - - -	0.25 0.20 0.30 0.25 0.50	Vdc
$ \begin{array}{l} \text{Base} - \text{Emitter Saturation Voltage (Note 3)} \\ \text{MMBT2369/A} \ (I_C = 10 \ \text{mAdc}, \ I_B = 1.0 \ \text{mAdc}) \\ \text{MMBT2369A} \ (I_C = 10 \ \text{mAdc}, \ I_B = 1.0 \ \text{mAdc}, \ T_A = -55^\circ\text{C}) \\ \text{MMBT2369A} \ (I_C = 30 \ \text{mAdc}, \ I_B = 3.0 \ \text{mAdc}) \\ \text{MMBT2369A} \ (I_C = 100 \ \text{mAdc}, \ I_B = 10 \ \text{mAdc}) \\ \end{array} $	V _{BE(sat)}	0.7 _ _ _	- - - -	0.85 1.02 1.15 1.60	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	_	_	4.0	pF
Small Signal CurrentGain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	h _{fe}	5.0	_	_	-
SWITCHING CHARACTERISTICS					
Storage Time ($I_{B1} = I_{B2} = I_C = 10 \text{ mAdc}$)	t _s	_	5.0	13	ns
Turn-On Time (V _{CC} = 3.0 Vdc, I _C = 10 mAdc, I _{B1} = 3.0 mAdc)	t _{on}	_	8.0	12	ns
Turn–Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t _{off}	-	10	18	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



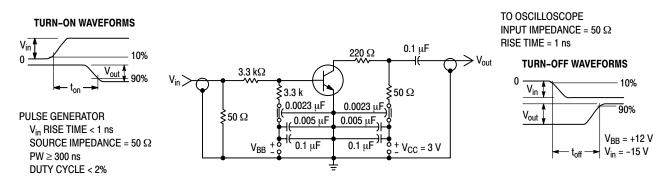


Figure 5. Turn-On and Turn-Off Time Test Circuit

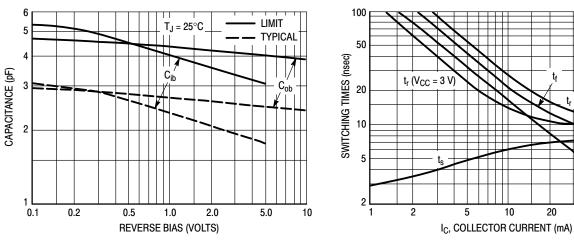


Figure 6. Junction Capacitance Variations



 $\beta_F = 10$

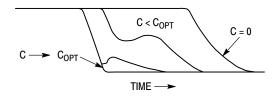
V_{CC} = 10 V

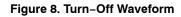
V_{OB} = 2 V

V_{CC} = 10 V

50

100





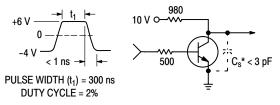
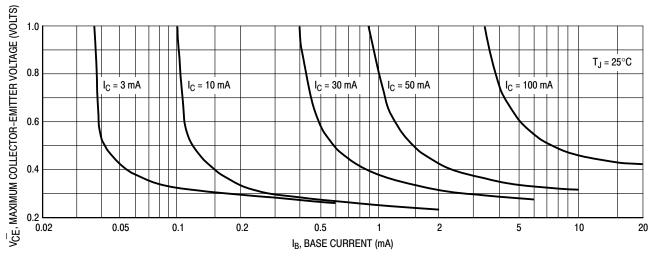


Figure 9. Storage Time Equivalent Test Circuit





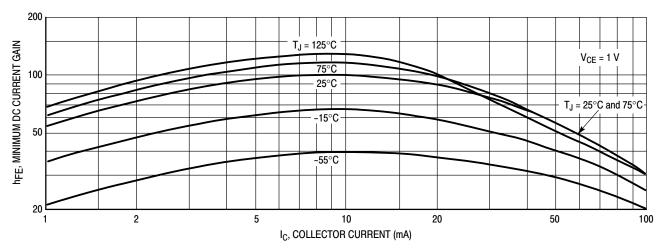


Figure 11. Minimum Current Gain Characteristics

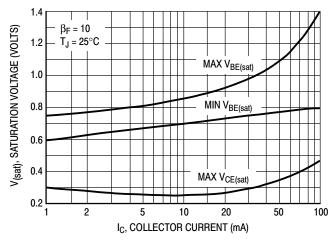


Figure 12. Saturation Voltage Limits





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